MC74VHC125

Quad Bus Buffer
with 3−State Control Inputs

The MC74VHC125 is a high speed CMOS quad bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.
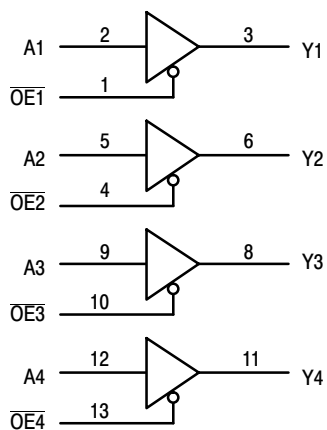
The MC74VHC125 requires the 3−state control input ($\overline{OE}$) to be set High to place the output into the high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: t_{PD} = 3.8ns (Typ) at V_{CC} = 5 V
- Low Power Dissipation: I_{CC} = 4 µA (Max) at T_A = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model; > 2000 V,
  Machine Model; > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates

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14−LEAD SOIC
D SUFFIX
CASE 751A

14−LEAD TSSOP
DT SUFFIX
CASE 948G
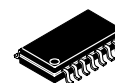
14−LEAD SOIC EIAJ
M SUFFIX
CASE 965

PIN CONNECTION AND MARKING DIAGRAM
(Top View)

$\overline{OE1}$	1 ●		14	V_{CC}
A1	2		13	$\overline{OE4}$
Y1	3		12	A4
$\overline{OE2}$	4		11	Y4
A2	5		10	$\overline{OE3}$
Y2	6		9	A3
GND	7		8	Y3
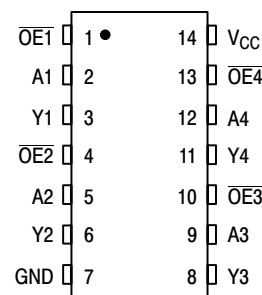
DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 6 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping
MC74VHC125D	SOIC	55 Units/Rail
MC74VHC125DT	TSSOP	96 Units/Rail
MC74VHC125M	SOIC EIAJ	50 Units/Rail

LOGIC DIAGRAM

Active−Low Output Enables

FUNCTION TABLE

VHC125		
Inputs		**Output**
A	**$\overline{OE}$**	**Y**
H	L	H
L	L	L
X	H	Z

MC74VHC125

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	−0.5 to +7.0	V
V_{in}	DC Input Voltage	−0.5 to +7.0	V
V_{out}	DC Output Voltage	−0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current	− 20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T_{stg}	Storage Temperature	−65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

** Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C
   TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		2.0	5.5	V
V_{in}	DC Input Voltage		0	5.5	V
V_{out}	DC Output Voltage		0	V_{CC}	V
T_A	Operating Temperature, All Package Types		−55	+125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 3.3 V ± 0.3 V V_{CC} =5.0 V ± 0.5 V	0 0	100 20	ns/V

MC74VHC125

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	$T_A = 25°C$ Min	Typ	Max	$T_A \leq 85°C$ Min	Max	$T_A \leq 125°C$ Min	Max	Unit
V_{IH}	Minimum High−Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V_{IL}	Maximum Low−Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V_{OH}	Minimum High−Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V_{OL}	Maximum Low−Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 4$ mA $I_{OL} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I_{OZ}	Maximum 3−State Leakage Current	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5			± 0.25		± 2.5		± 2.5	μA
I_{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5V$ or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40		40	μA

MC74VHC125

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	Test Conditions		$T_A = 25°C$			$T_A = \leq 85°C$		$T_A = \leq 125°C$		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3V$	$C_L = 15$ pF $C_L = 50$ pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0	1.0 1.0	12.0 16.0	ns
		$V_{CC} = 5.0 \pm 0.5V$	$C_L = 15$ pF $C_L = 50$ pF		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	8.5 10.5	
t_{PZL}, t_{PZH}	Maximum Output Enable TIme, $\overline{OE}$ to Y	$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1$ kΩ	$C_L = 15$ pF $C_L = 50$ pF		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0	1.0 1.0	11.5 15.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1$ kΩ	$C_L = 15$ pF $C_L = 50$ pF		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0	1.0 1.0	7.5 9.5	
t_{PLZ}, t_{PHZ}	Maximum Output Disable Time, $\overline{OE}$ to Y	$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1$ kΩ	$C_L = 50$ pF		9.5	13.2	1.0	15.0	1.0	18.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1$ kΩ	$C_L = 50$ pF		6.1	8.8	1.0	10.0	1.0	12.0	
t_{OSLH}, t_{OSHL}	Output–to–Output Skew	$V_{CC} = 3.3 \pm 0.3V$ (Note 1)	$C_L = 50$ pF			1.5		1.5		1.5	ns
		$V_{CC} = 5.0 \pm 0.5V$ (Note 1)	$C_L = 50$ pF			1.0		1.0		1.0	
C_{in}	Maximum Input Capacitance				4	10		10		10	pF
C_{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)				6						pF

		Typical @ 25°C, $V_{CC} = 5.0$ V	
C_{PD}	Power Dissipation Capacitance (Note 2)	14	pF

1. Parameter guaranteed by design. $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$.
2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$ (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

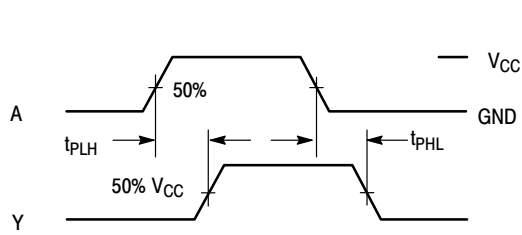| Symbol	Characteristic	$T_A = 25°C$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.8	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.3	−0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

MC74VHC125

SWITCHING WAVEFORMS
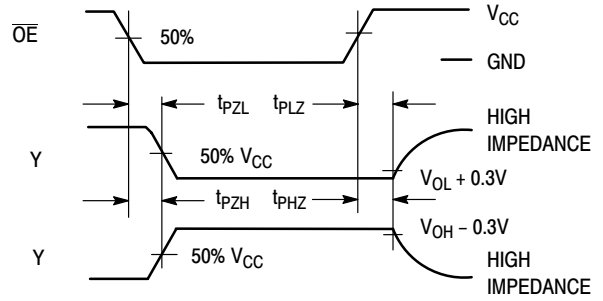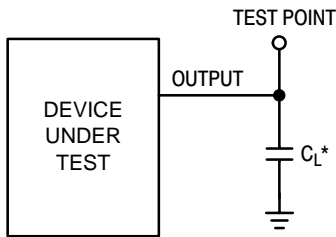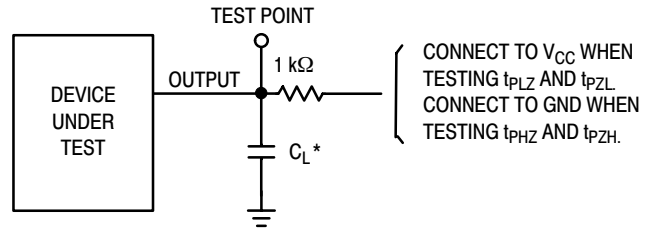

Figure 1.

Figure 2.

*Includes all probe and jig capacitance

Figure 3. Test Circuit

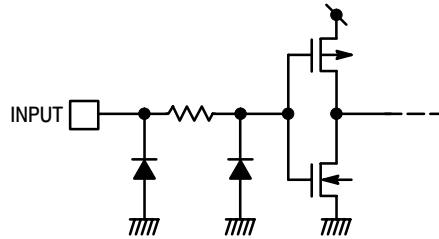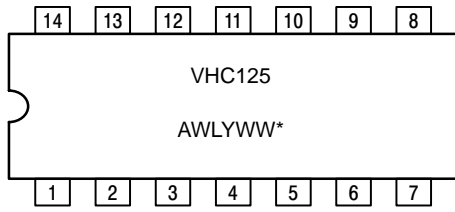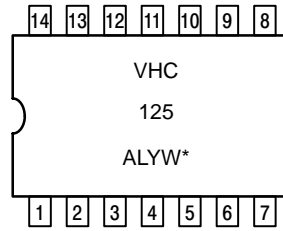*Includes all probe and jig capacitance

Figure 4. Test Circuit

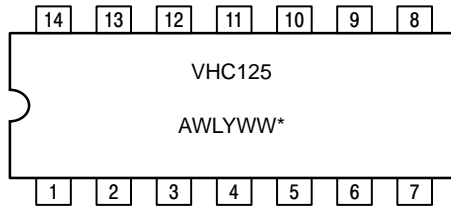**Figure 5. Input Equivalent Circuit**

MC74VHC125

MARKING DIAGRAMS
(Top View)

```
 ┌14┐ ┌13┐ ┌12┐ ┌11┐  ┌10┐  ┌9┐   ┌8┐
┌──────────────────────────────────────┐
│                                        │
│               VHC125                   │
⟩                                        │
│              AWLYWW*                    │
│                                        │
└──────────────────────────────────────┘
 └1┘  └2┘  └3┘  └4┘   └5┘   └6┘   └7┘
```

14–LEAD SOIC
D SUFFIX
CASE 751A

```
 ┌14┐┌13┐┌12┐┌11┐┌10┐┌9┐┌8┐
┌────────────────────────────┐
│                            │
│          VHC               │
⟩         125                │
│         ALYW*              │
│                            │
└────────────────────────────┘
 └1┘└2┘└3┘└4┘└5┘└6┘└7┘
```

14–LEAD TSSOP
DT SUFFIX
CASE 948G

```
 ┌14┐ ┌13┐ ┌12┐ ┌11┐ ┌10┐  ┌9┐   ┌8┐
┌──────────────────────────────────────┐
│                                        │
│               VHC125                   │
⟩                                        │
│              AWLYWW*                    │
│                                        │
└──────────────────────────────────────┘
 └1┘  └2┘  └3┘  └4┘  └5┘   └6┘   └7┘
```

14–LEAD SOIC EIAJ
M SUFFIX
CASE 965

*See Applications Note AND8004/D for date code and traceability information.

MC74VHC125

PACKAGE DIMENSIONS
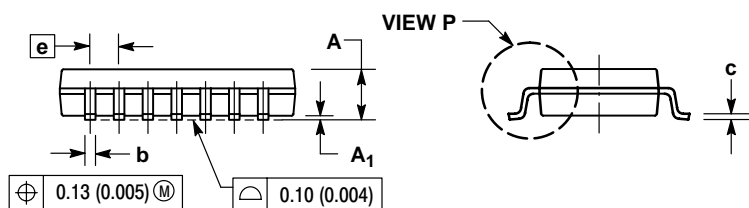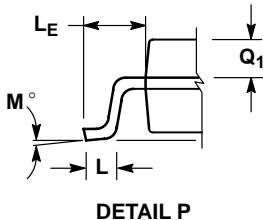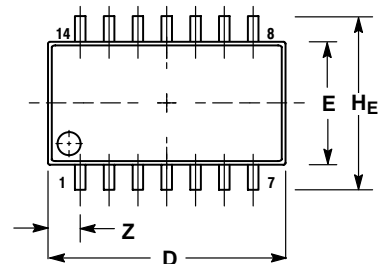
SOIC–14
D SUFFIX
CASE 751A–3
ISSUE F
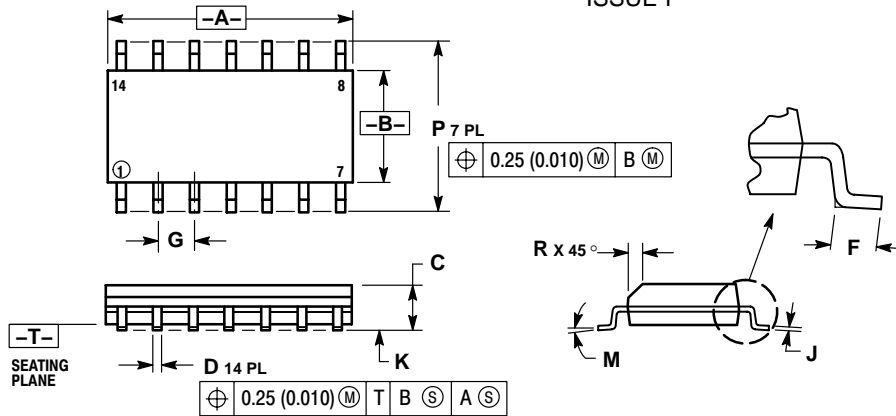
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP
DT SUFFIX
CASE 948G–01
ISSUE O
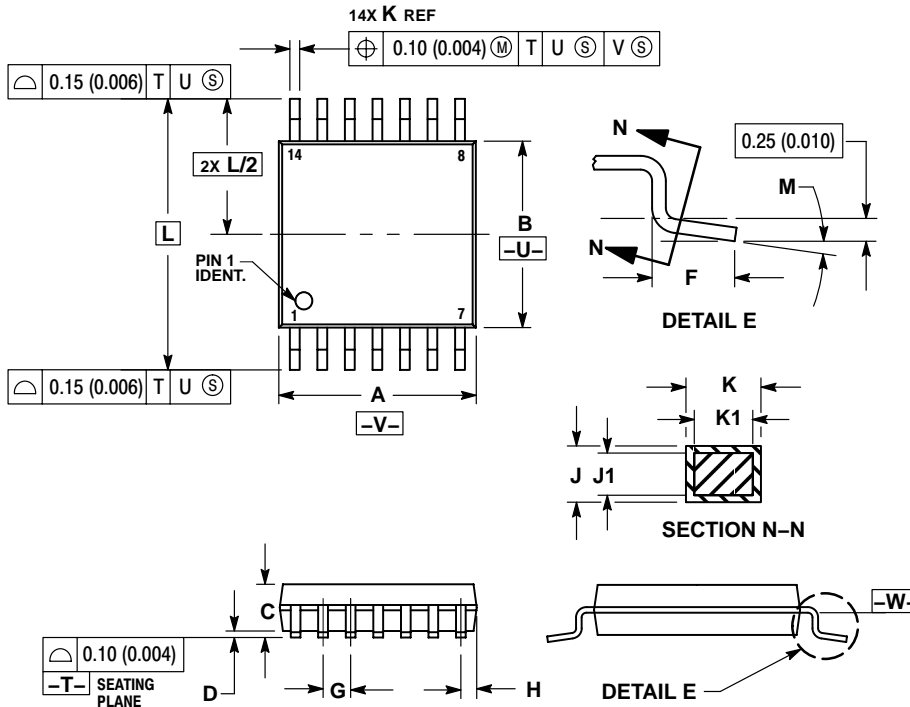
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

DETAIL E

SECTION N–N

MC74VHC125

PACKAGE DIMENSIONS

SO–14
M SUFFIX
CASE 965–01
ISSUE O

DETAIL P

VIEW P

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056